

AMENDMENTS TO THE CLAIMS

1-12. (canceled)

13. (currently amended) A method of fabricating a semiconductor light-emitting element comprising:

~~a chip having~~ forming said semiconductor light-emitting element including at least an electrode and a protective film layer;

~~an insulating resin for sealing said chip~~ light-emitting element with an insulating resin;

~~wherein hardening~~ said insulating resin ~~is hardened~~ at high temperature; and

~~heat-treated~~ heat-treating said light-emitting element in an atmosphere having an absolute humidity H (KPa) during the time T (hr) satisfying $T \geq -1.7H + 124$.

14. (new) A method of fabricating a semiconductor light-emitting element according to claim 13, wherein said absolute humidity H (KPa) is not less than 10 KPa.

15. (new) A method of fabricating a semiconductor light-emitting element according to claim 13, wherein said absolute humidity H (KPa) is not less than 50 KPa.